Dual N-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

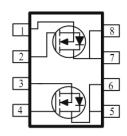
- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- · White LED boost converters





V_{DS} (V)

100



I_D(A)

4.2

4.0

PRODUCT SUMMARY

 $r_{DS(on)}(\overline{m\Omega})$

81 @ V_{GS} = 10V

92 @ V_{GS} = 4.5V

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Dusin Commenta	T _A =25°C		4.2		
Continuous Drain Current ^a	T _A =70°C	l _D	3.3	Α	
ulsed Drain Current ^b		I _{DM}	30		
Continuous Source Current (Diode Conduction) a		Is	3	Α	
Device Discinction ^a	T _A =25°C		2.1	W	
Power Dissipation ^a	T _A =70°C	r _D	1.3	VV	
Operating Junction and Storage Temperature Range	-	T_J, T_{stq}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W		
	Steady State	IXOJA	110	C/VV		

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

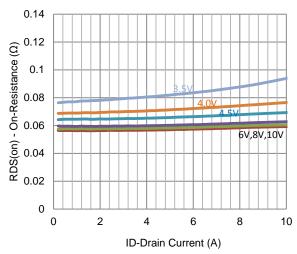
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1		3.5	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 2.9 \text{ A}$			81	mΩ
	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.6 \text{ A}$			92	11122
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 2.9 \text{ A}$		20		S
Diode Forward Voltage	V_{SD}	$I_S = 1.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V
Dynamic						
Total Gate Charge	Q_g			17		
Gate-Source Charge	Q_gs	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 2.9 \text{ A}$		3.3		nC
Gate-Drain Charge	Q_{gd}			8.7		
Turn-On Delay Time	t _{d(on)}			7		
Rise Time	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 15 \Omega, \text{ I}_{D} = 2.9 \text{ A},$		6.7		ns
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = 10 V, R_{GEN} = 6 Ω		45		
Fall-Time	t _f			23		
Input Capacitance	C _{iss}			990		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		115		pF
Reverse Transfer Capacitance	C_{rss}			77		

Notes

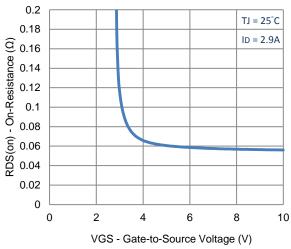
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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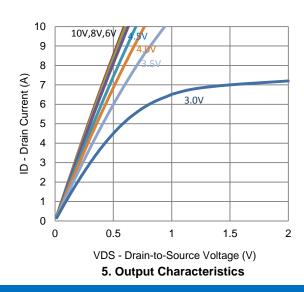
Typical Electrical Characteristics

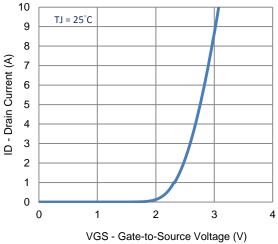


1. On-Resistance vs. Drain Current

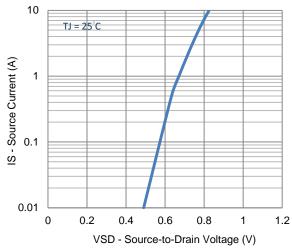


3. On-Resistance vs. Gate-to-Source Voltage

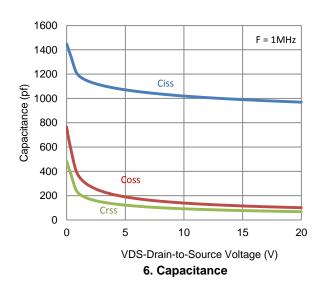




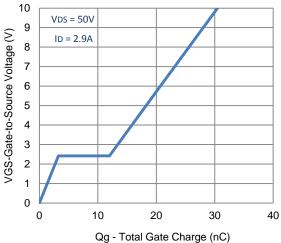
2. Transfer Characteristics



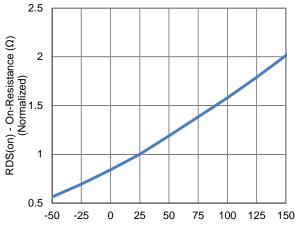
4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics

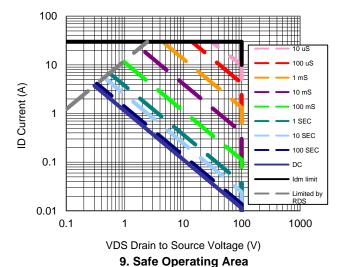


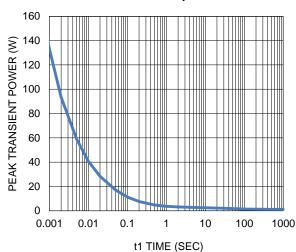




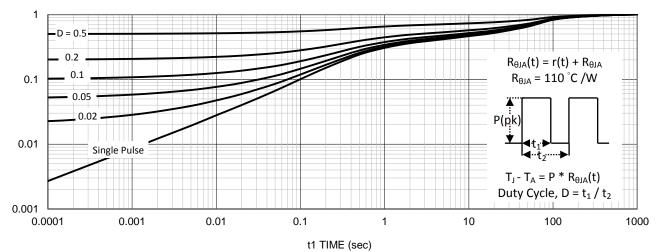
TJ - Junction Temperature (°C)

8. Normalized On-Resistance Vs **Junction Temperature**





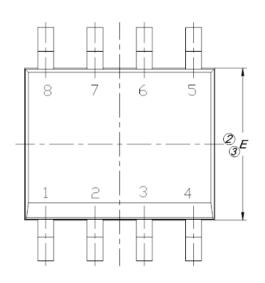
10. Single Pulse Maximum Power Dissipation

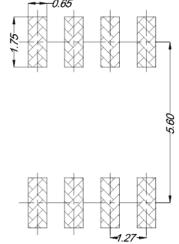


11. Normalized Thermal Transient Junction to Ambient

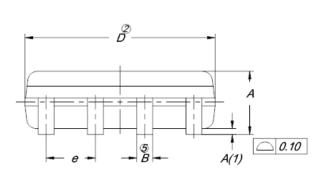
Package Information

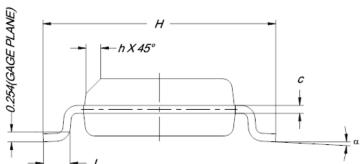
Land Pattern (Only for Reference)





DIM.	MILLIMETERS				
	MIN.	NOM.	MAX.		
Α	1.35	1.55	1.75		
A(1)	0.10	0.18	0.25		
В	0.38	0.45	0.51		
С	0.19	0.22	0.25		
D	4.80	4.90	5.00		
E	3.80	3.90	4.00		
е	1.27 BSC				
Н	5.80	6.00	6.20		
L	0.50	0.72	0.93		
α	0°	4°	8°		
h	0.25	0.38	0.50		





Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess
 Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The
 Foot.